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ON Semiconductor
MMBD2835LT1

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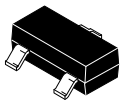
MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

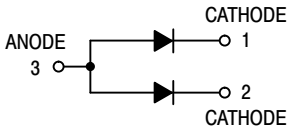
Monolithic Dual Switching Diodes

ON Semiconductor®

http://onsemi.com



SOT−23 (TO−236AB)
CASE 318−08
STYLE 12



Features

- AEC−Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage MMBD2835LT1G, SMMBD2835LT1G MMBD2836LT1G	V_R	 35 75	Vdc
Forward Current	I_F	100	mAdc

THERMAL CHARACTERISTICS

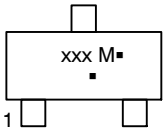
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



xxx = Specific Device Code
A3X = MMBD2835LT1G
SMMBD2835LT1G
A2X = MMBD2836LT1G
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBD2835LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBD2835LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBD2836LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel

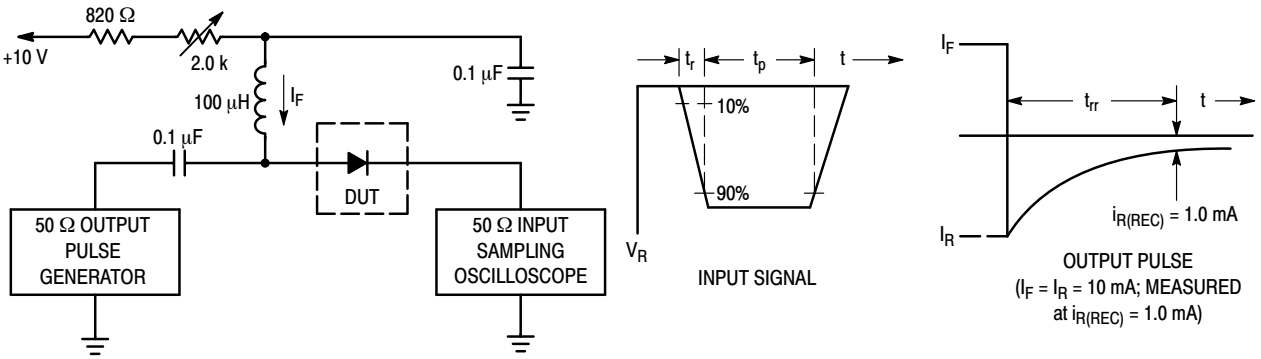
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) **(EACH DIODE)**

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage (I_R = 100 μAdc) MMBD2835LT1G, SMMBD2835LT1G MMBD2836LT1G	$V_{(BR)}$	 35 75	 – –	Vdc
Reverse Voltage Leakage Current (Note 3) (V_R = 30 Vdc) MMBD2835LT1G, SMMBD2835LT1G (V_R = 50 Vdc) MMBD2836LT1G	I_R	 – –	 100 100	nAdc
Diode Capacitance (V_R = 0 V, f = 1.0 MHz)	C_T	–	4.0	pF
Forward Voltage (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 100 mAdc)	V_F	 – – –	 1.0 1.0 1.2	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc) (Figure 1)	t_{rr}	–	4.0	ns

3. For each individual diode while the second diode is unbiased.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH CATHODE

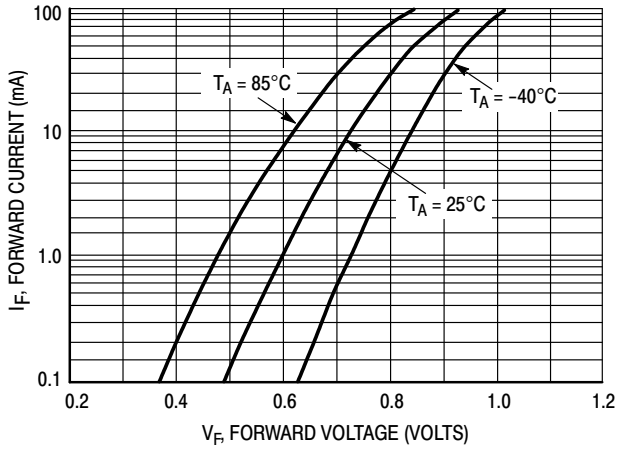


Figure 2. Forward Voltage

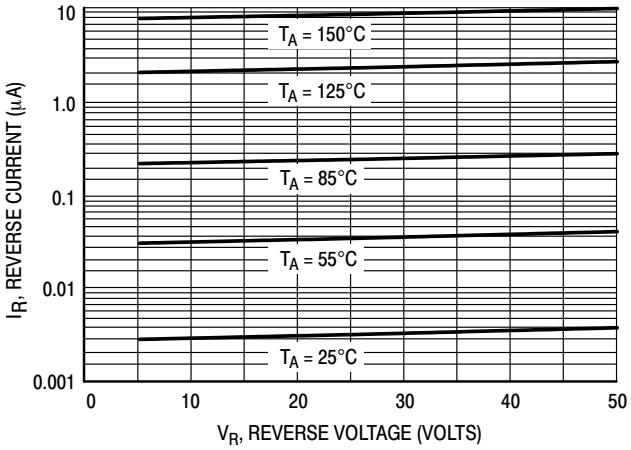


Figure 3. Leakage Current

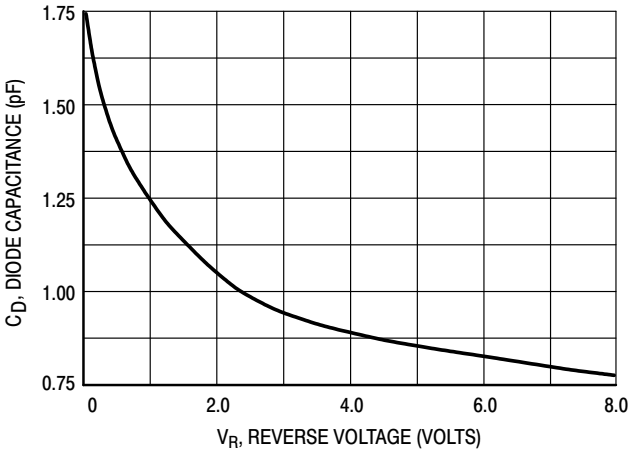
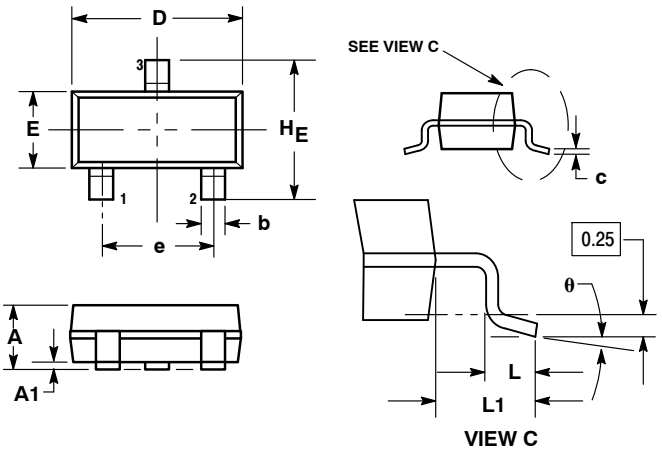


Figure 4. Capacitance

MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AP

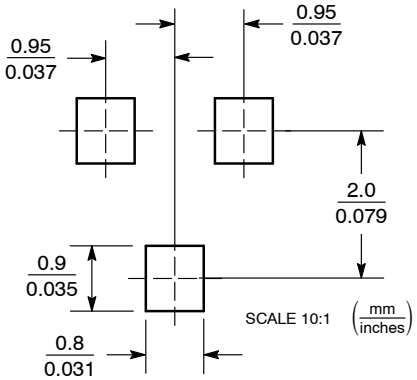


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	−−−	10°	0°	−−−	10°

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

SOLDERING FOOTPRINT



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